

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-6.5	A
		T <sub>A</sub> = +70°C		-5.2	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-26	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	—	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	40	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5.8A
		—	—	70		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3.8A
Forward Transconductance	g <sub>fs</sub>	—	9	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -4.6A
Diode Forward Voltage	V <sub>SD</sub>	-0.5	-0.72	-1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.1A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	820	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	200	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	160	—	pF	
Gate Resistance	R <sub>g</sub>	—	10.4	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	14.4	—	nC	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V I <sub>D</sub> = -4.5A
Gate-Source Charge	Q <sub>gs</sub>	—	2.6	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.7	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	13.7	—	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 6Ω, R <sub>L</sub> = 10Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>r</sub>	—	14.0	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	79.1	—		
Turn-Off Fall Time	t <sub>f</sub>	—	35.5	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

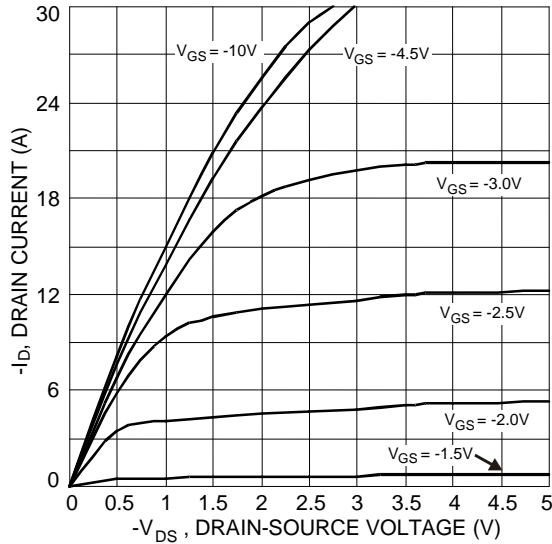


Fig. 1 Typical Output Characteristic

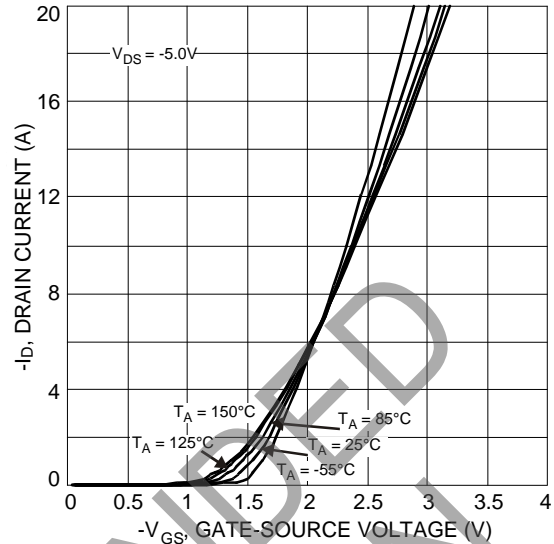


Fig. 2 Typical Transfer Characteristic

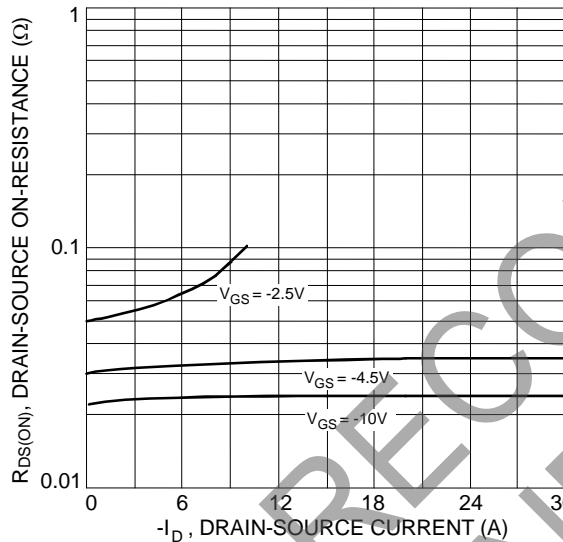


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

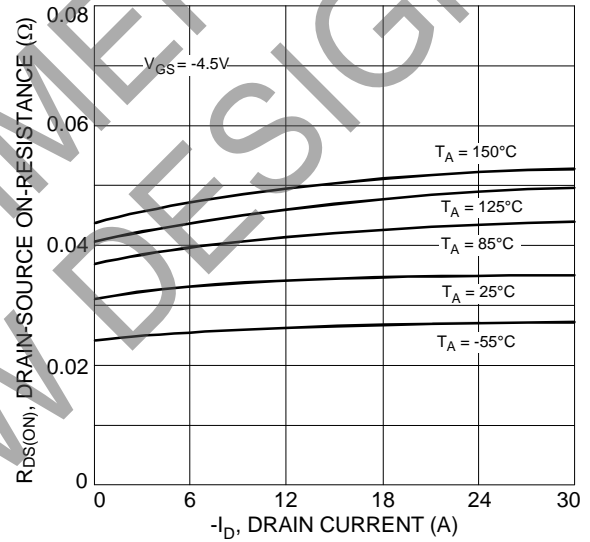


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

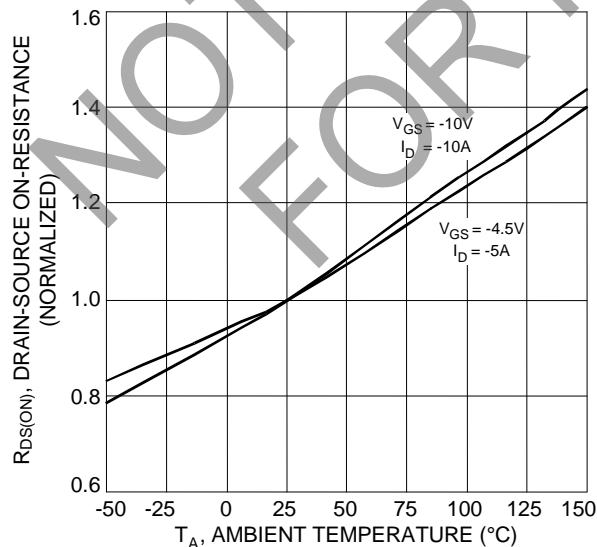


Fig. 5 Normalized On-Resistance vs. Ambient Temperature

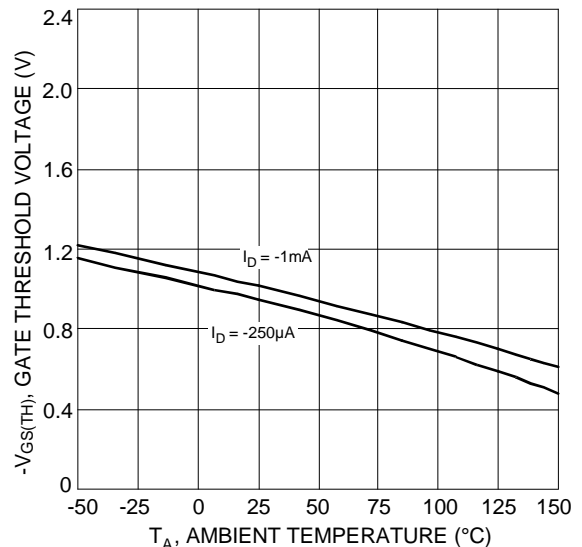


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

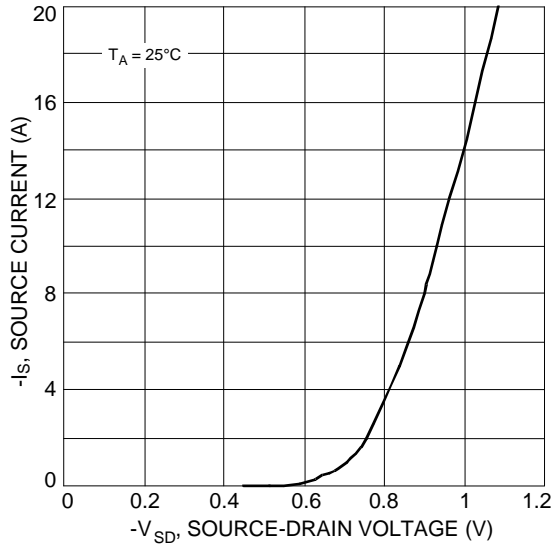


Fig. 7 Diode Forward Voltage vs. Current

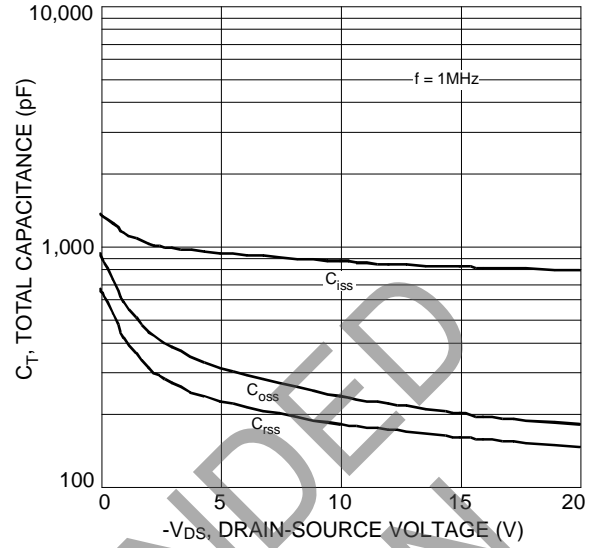


Fig. 8 Typical Total Capacitance

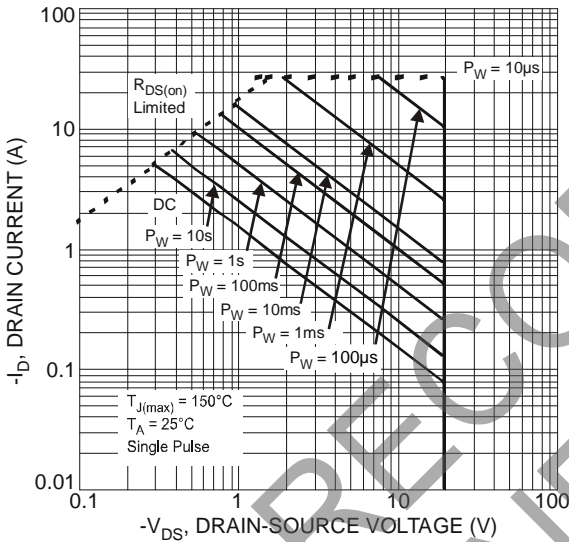
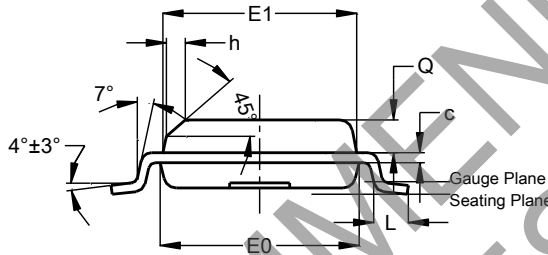
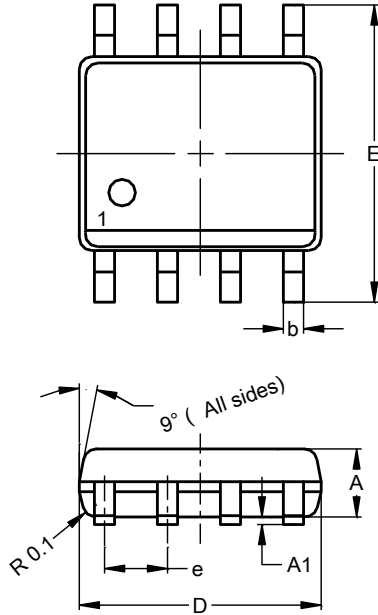


Fig. 9 SOA, Safe Operation Area

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

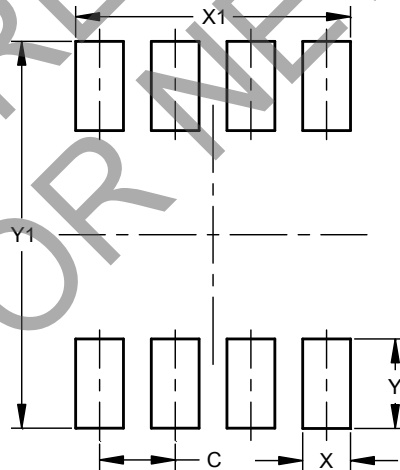


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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